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Title: 3-GRID NEUTRAL BEAM
SOURCE USED FOR ETCHING
SEMICONDUCTOR DEVICE
Inventor(s): Geun-Young YEOM et al.
DOCKET NO.: 061887-0119

FIG. 1

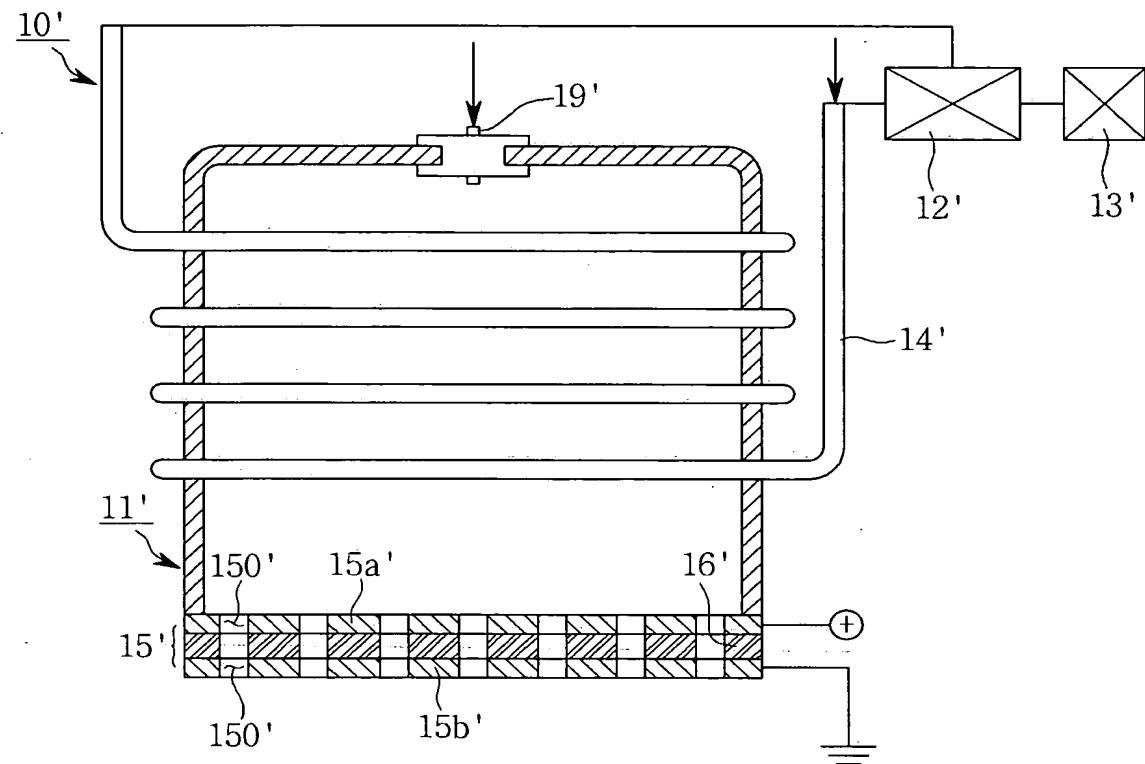
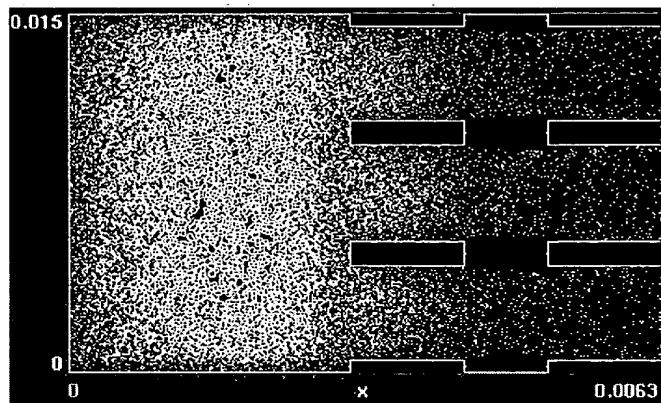


FIG. 2A



5 FIG. 2B

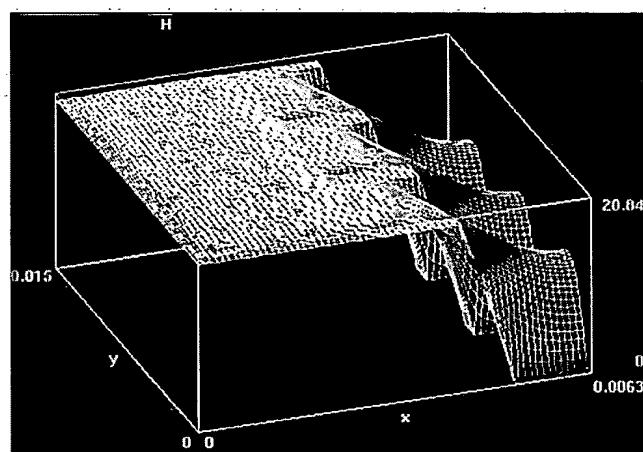
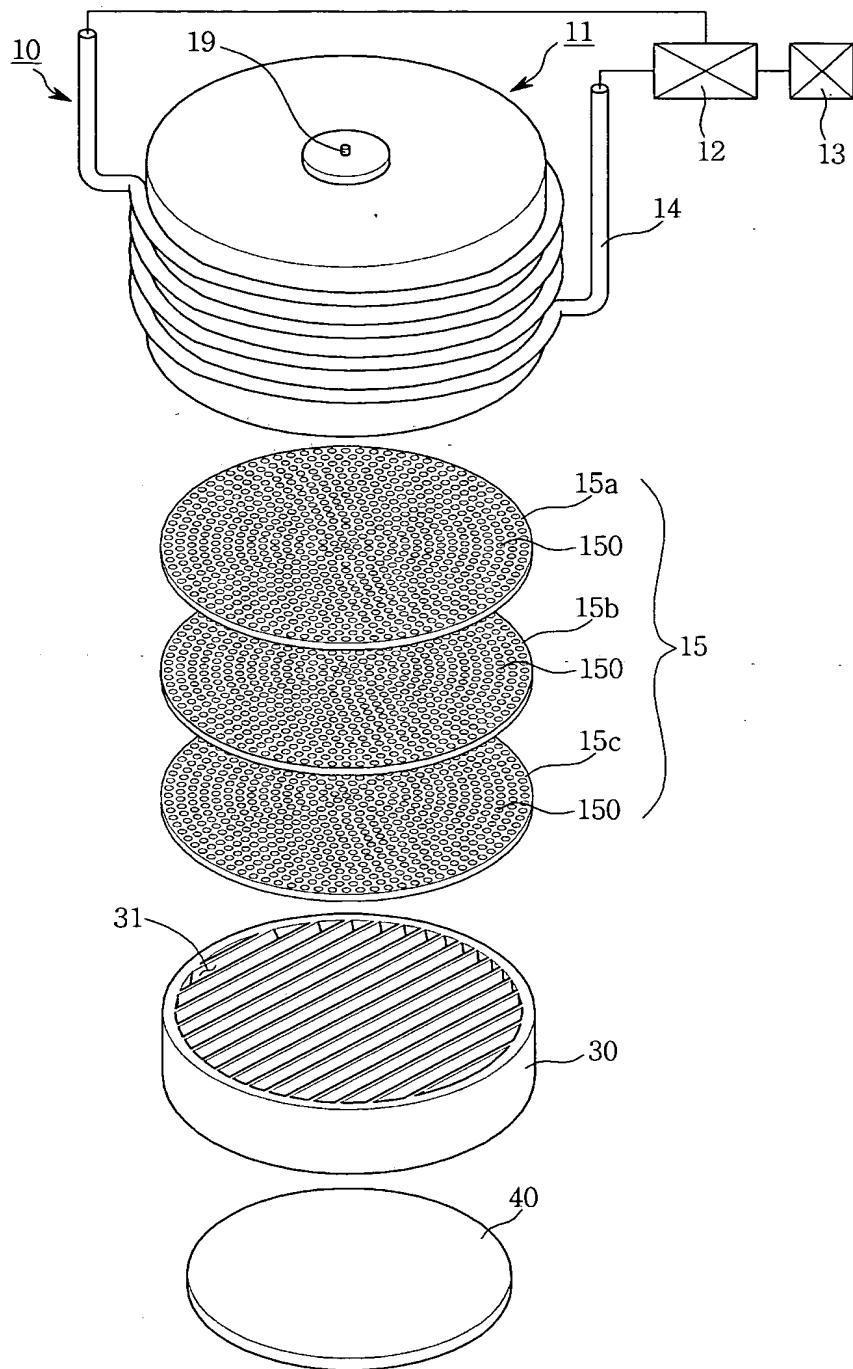


FIG. 3



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FIG. 4

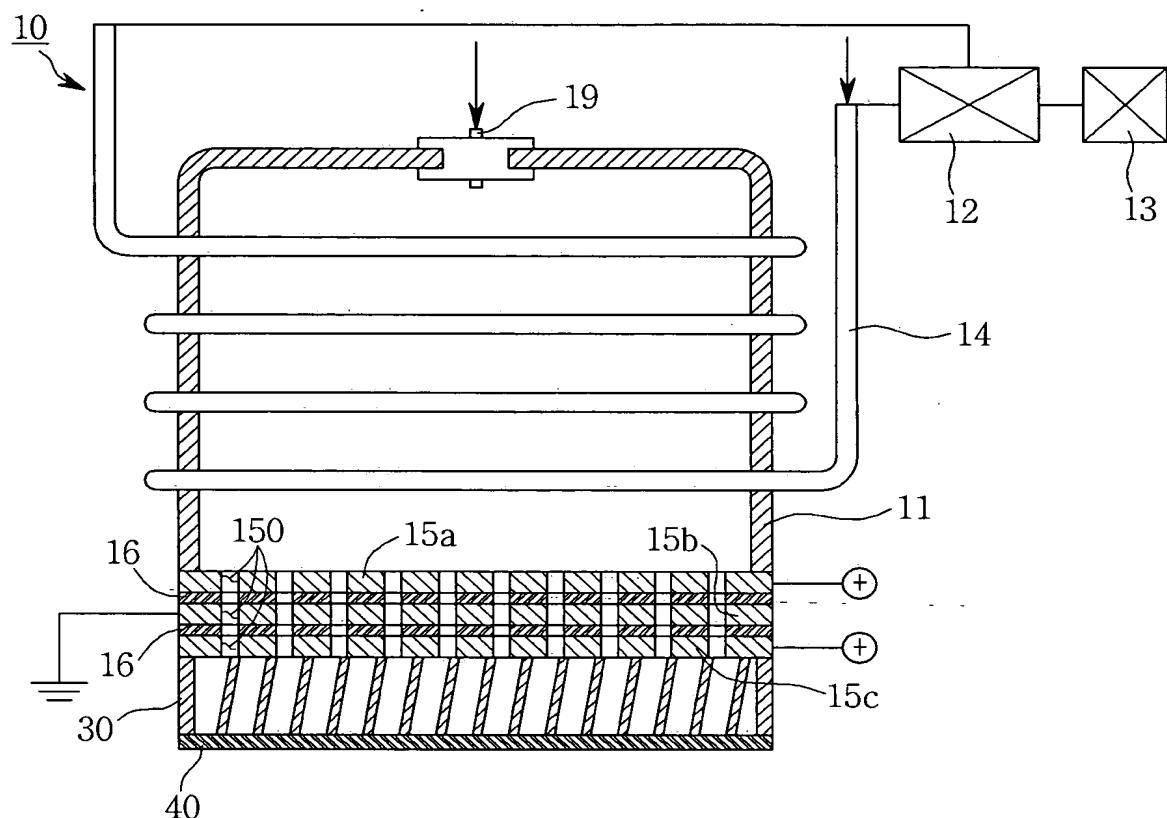
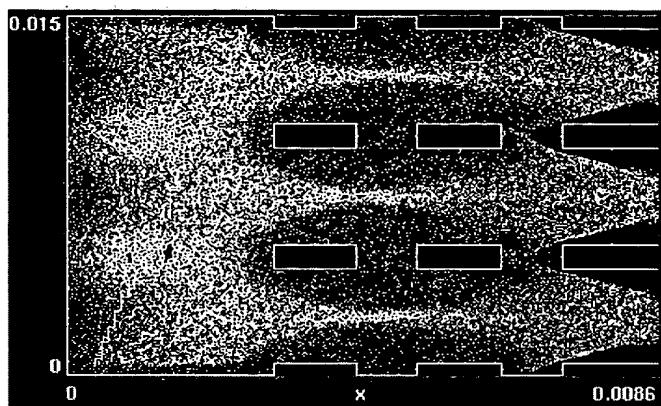


FIG. 5A



5 FIG. 5B

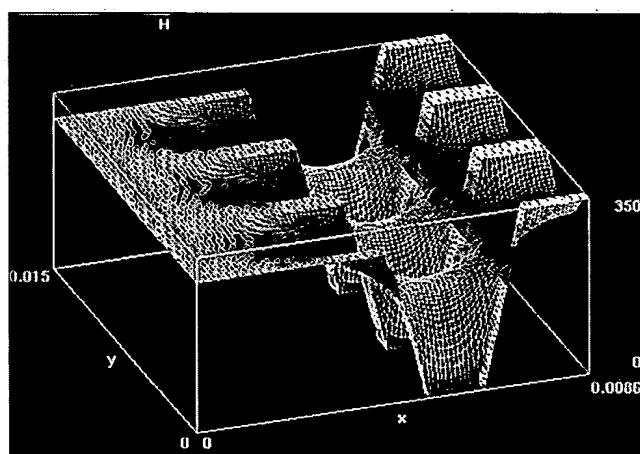


FIG. 6

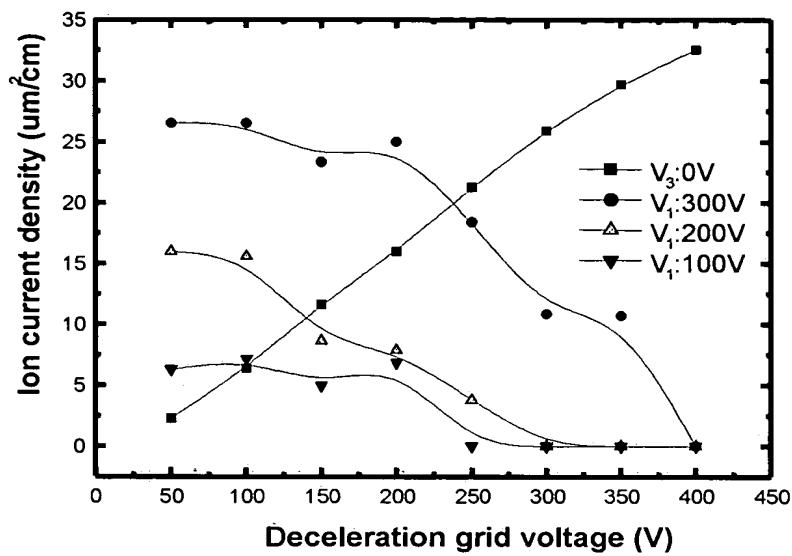


FIG. 7A

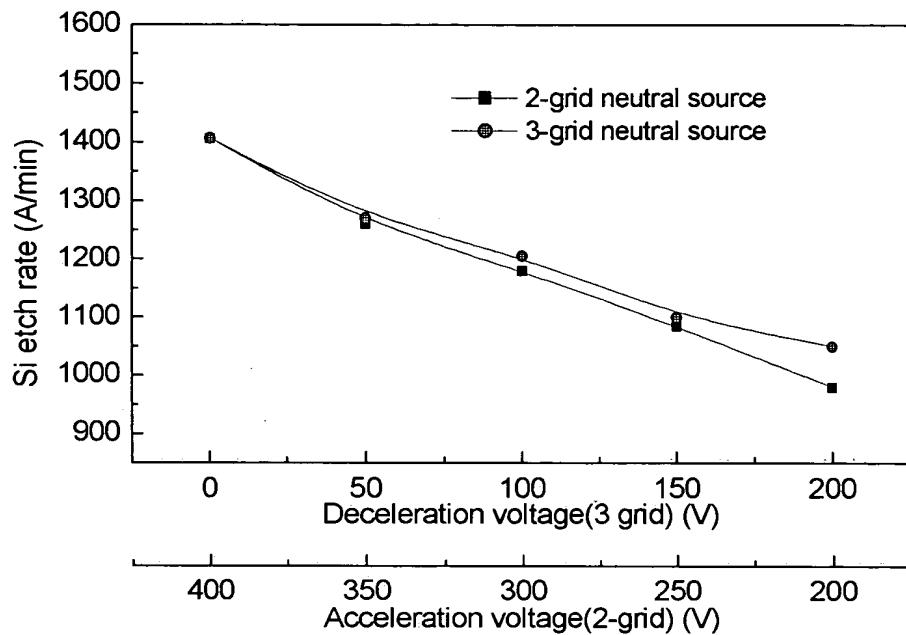


FIG. 7B

